NSN 5961-01-277-2620

Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-277-2620 **Inclosure Material:** Ceramic **Overall Length:** Between 0.745 inches and 0.830 inches **Overall Height:** 0.240 inches **Overall Width:** 0.552 inches **Mounting Facility Quantity: Component Name And Quantity:** 2 transistor **Mounting Method:** Unthreaded hole **Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 65.0 drain to gate voltage all transistor and 65.0 drain to source voltage all transistor and 20.0 gate to source voltage all transistor **Current Rating Per Characteristic:** 4.00 amperes source cutoff current of standard range all transistor **Power Rating Per Characteristic:** 20.0 watts small-signal input power, common-collector absolute all transistor **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** Case contains beryllium oxide - handle and dispose iaw hazmat procedures **Precious Material And Location:** Terminal surfaces gold **Precious Material:** Gold **Test Data Document:** 80063-a3012715 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 4 ribbon Shelf Life: N/a **Unit Of Measure:**

No **Fiig:**

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Demilitarization: